



## A5A:820.XX

### VOLTAGE RATINGS

Part Number	V <sub>RRM</sub> , V <sub>R</sub> (V) Max. rep. peak reverse voltage		V <sub>RSM</sub> , V <sub>R</sub> (V) Max. non-rep. peak reverse voltage
	T <sub>J</sub> = 0 to 175°C	T <sub>J</sub> = -40 to 0°C	T <sub>J</sub> = 25 to 175°C
A5A:820.24	2400	2400	2500
A5A:820.26	2600	2600	2700
A5A:820.28	2800	2800	2900
A5A:820.30	3000	3000	3100
A5A:820.32	3200	3200	3300
A5A:820.34	3400	3400	3500
A5A:820.36	3600	3600	3700
A5A:820.38	3800	3800	3900
A5A:820.40	4000	4000	4100
A5A:820.42	4200	4200	4300

### MAXIMUM ALLOWABLE RATINGS

PARAMETER	VALUE	UNITS	NOTES
T <sub>J</sub> Junction Temperature	-40 to 175	°C	-
T <sub>stg</sub> Storage Temperature	-40 to 175	°C	-
I <sub>F(AV)</sub> Max. Av. current	630	A	180° half sine wave
@ Max. T <sub>C</sub>	125	°C	
I <sub>F(RMS)</sub> Nom. RMS current	1250	A	-
I <sub>FSM</sub> Max. Peak non-rep. surge current	12.80 13.95 15.23 16.60	kA	50 Hz half cycle sine wave Initial T <sub>J</sub> = 175°C, rated V <sub>RRM</sub> applied after surge. 60 Hz half cycle sine wave 50 Hz half cycle sine wave Initial T <sub>J</sub> = 175°C, no voltage applied after surge. 60 Hz half cycle sine wave
I <sup>2</sup> t Max. I <sup>2</sup> t capability	7510 8190 10550 11500	kA <sup>2</sup> s	t = 10ms Initial T <sub>J</sub> = 175°C, rated V <sub>RRM</sub> applied after surge. t = 8.3 ms t = 10ms Initial T <sub>J</sub> = 175°C, no voltage applied after surge. t = 8.3 ms
I <sup>2</sup> t <sup>1/2</sup> Max. I <sup>2</sup> t <sup>1/2</sup> capability	12600	kA <sup>2</sup> s <sup>1/2</sup>	Initial T <sub>J</sub> = 175°C, no voltage applied after surge. $\int t$ for time t <sub>x</sub> = I <sup>2</sup> t <sup>1/2</sup> * t <sub>x</sub> <sup>1/2</sup> . (0.1 < t <sub>x</sub> < 10ms).
F Mounting Force	1250	N.m	-



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### CHARACTERISTICS

PARAMETER	MIN.	TYP.	MAX.	UNITS	TEST CONDITIONS
$V_{FM}$ Peak forward voltage	---	1.60	1.89	V	Initial $T_J = 25^\circ\text{C}$ , 50-60Hz half sine, $I_{peak} = 1979\text{A}$ .
$V_{F(TO)1}$ Low-level threshold	---	---	0.824	V	$T_J = 175^\circ\text{C}$
$V_{F(TO)2}$ High-level threshold	---	---	0.871		$\text{Av. power} = V_{F(TO)} * I_{F(AV)} + r_F * [I_{F(RMS)}]^2$
$r_{F1}$ Low-level resistance	---	---	0.459	m	Use low values for $I_{FM} < I_{F(AV)}$
$r_{F2}$ High-level resistance	---	---	0.279		
$I_{RM}$ Peak reverse current	---	15	75	mA	$T_J = 175^\circ\text{C}$ . Max. rated $V_{RRM}$
$R_{thJC}$ Thermal resistance, junction-to-case	---	---	0.050	°C/W	DC operation, double side
	---	---	0.054	°C/W	180° sine wave, double side
	---	---	0.055	°C/W	120° rectangular wave, double side
$R_{thCS}$ Thermal resistance, case-to-sink	---	---	0.015	°C/W	Mtg. Surface smooth, flat and greased.
wt Weight	---	85(3.0)	---	g(oz.)	---
Case Style	TO-200AC				---

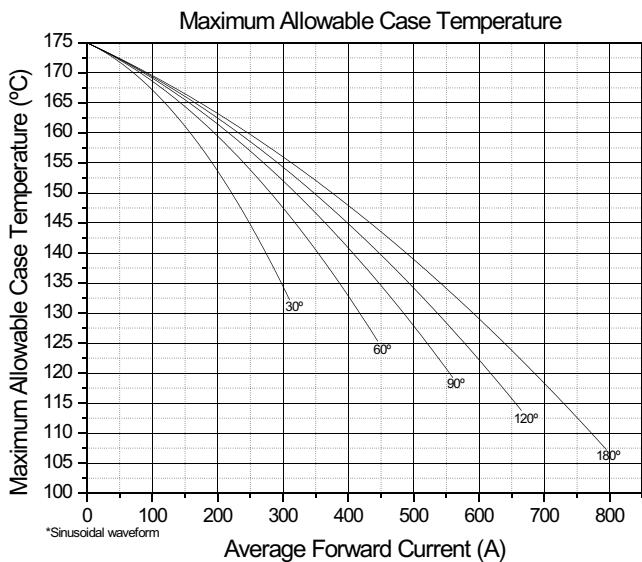


Fig. 1 - Current Ratings Characteristics

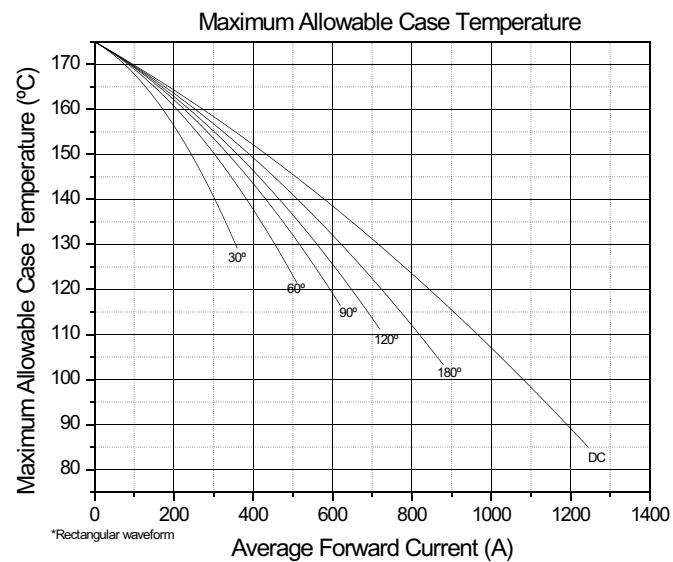
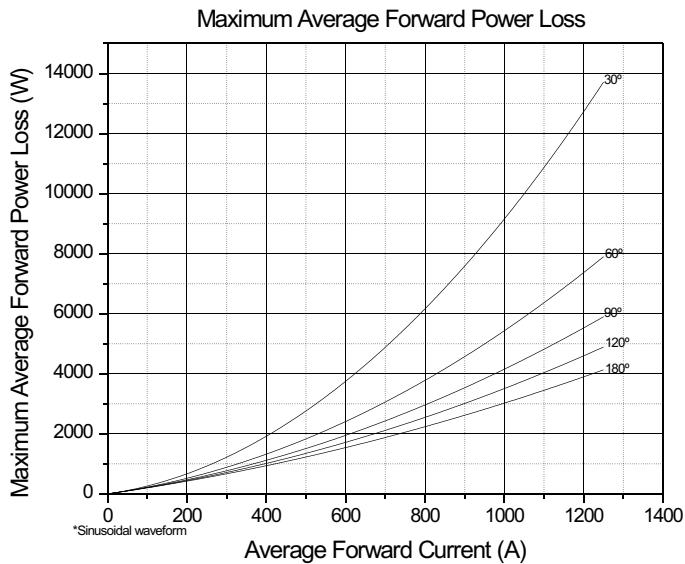


Fig. 2 - Current Ratings Characteristics

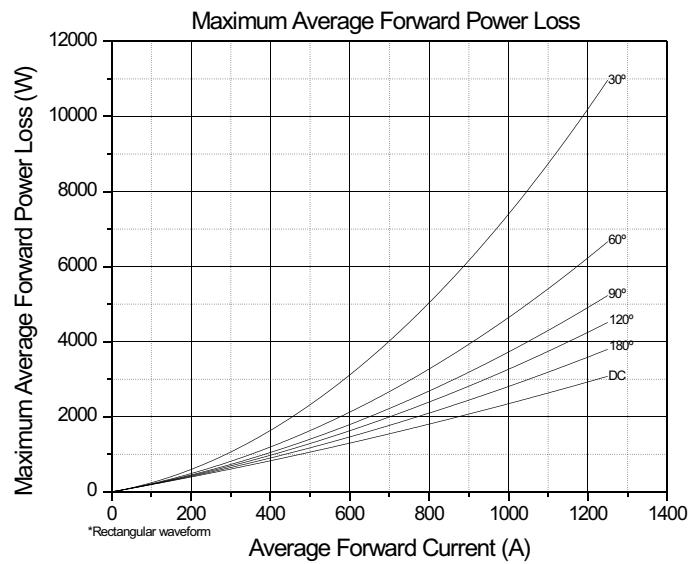


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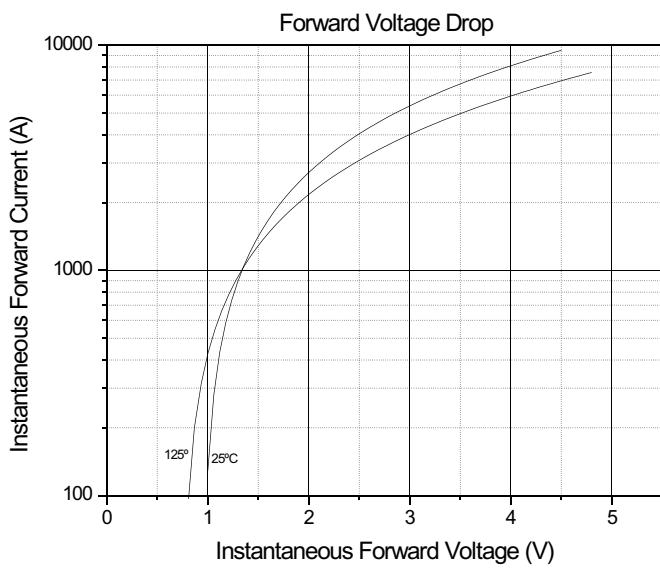
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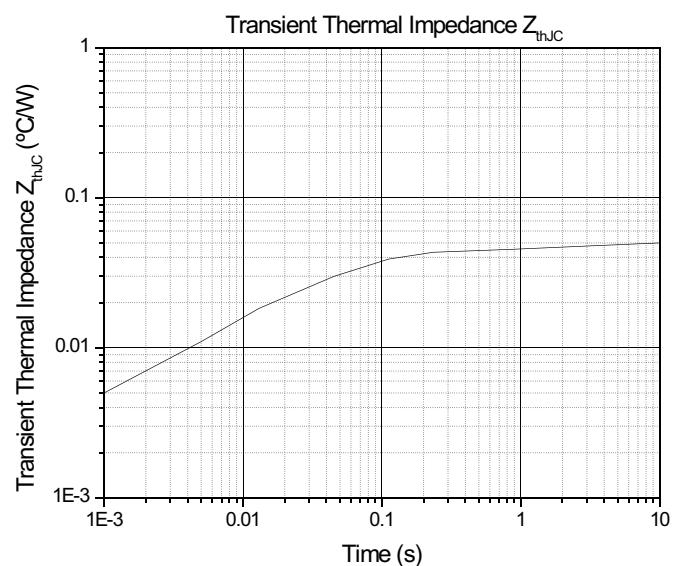
**Fig. 3 - On-State Power Loss Characteristics**



**Fig. 4 - On-State Power Loss Characteristics**



**Fig. 5 - Forward Voltage Drop Characteristics**



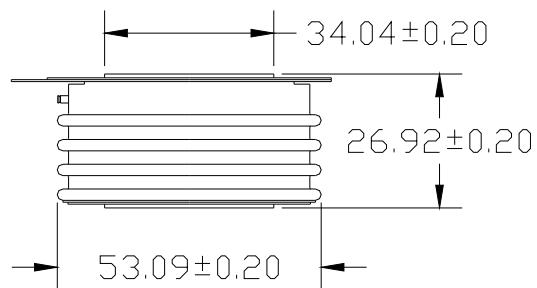
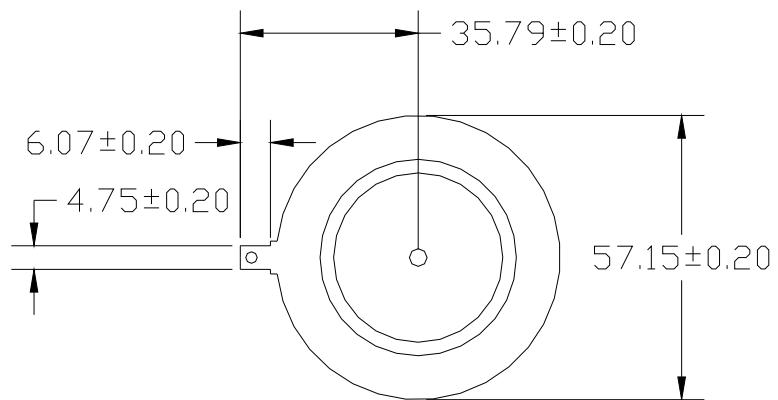
**Fig. 6 - Transient Thermal Impedance Characteristics**



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**TO-200AC**



**Fig. 7 - Outline Characteristics**